

Application No. 10/721,126

IN THE SPECIFICATION:

After the title, add the following paragraph:

**SPECIFIC DATA RELATED TO THE INVENTION**

This application is a continuation of U.S. application number 10/026,257 filed December 21, 2001, <sup>^</sup> NOW ABANDONED.

Amend as follows:

Page 1, beginning at line 5:

Several different dual damascene processes may be utilized in the fabrication of interconnect structures. One such process is the full via-first ("FVF"), which is illustrated in FIGS. 1 through 4. As shown in FIG. 1, a structure 10 prior to etching may have an interconnect layer 11 in which there is formed a metal interconnect feature 48 8. Overlaying layer 11 and feature 48 8 is a barrier layer 14. Over barrier layer 14 are two dielectric layers 12 and 13 separated by an intermediate etch stop layer 15. A patterned photoresist ("PR") layer 18 is deposited over top dielectric layer 13.

Page 6, beginning at line 10:

The mask films' composition are such that the first mask film has etch properties that are substantially identical to the etch properties of the third mask film while the second mask film has an etch properties that are substantially identical to the etch properties of the fourth mask film. The term "etch properties" as used in this specification are those characteristics of a film or layer composition including the etch rate and etch selectivity for a given etch chemistry and/or etching procedure.